



FTD7011 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 1.8V drive.
- Mount height 1.1mm.
- Coposite type, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-12	V
Gate-to-Source Voltage	V_{GSS}		± 10	V
Drain Current (DC)	I_D		-7	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-30	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (1000mm ² ×0.8mm) 1unit	1.2	W
Total Dissipation	P_T	When mounted on ceramic substrate (1000mm ² ×0.8mm)	1.3	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS} = 0\text{V}$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8\text{V}$, $V_{GS} = 0\text{V}$			-1	μA
		$V_{DS} = -12\text{V}$, $V_{GS} = 0\text{V}$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8\text{V}$, $V_{DS} = 0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -6\text{V}$, $I_D = -1\text{mA}$	-0.4		-1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -6\text{V}$, $I_D = -6\text{A}$	10	18		S

Marking : D7011

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FTD7011

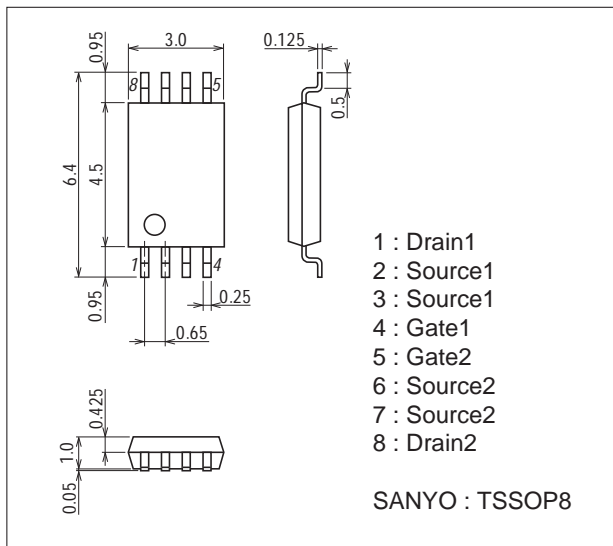
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -3A, V_{GS} = -4.5V$		14	19	$m\Omega$
	$R_{DS(on)2}$	$I_D = -1.5A, V_{GS} = -2.5V$		20	28	$m\Omega$
	$R_{DS(on)3}$	$I_D = -0.5A, V_{GS} = -1.8V$		32	56	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -6V, f = 1MHz$		1780		μF
Output Capacitance	C_{oss}	$V_{DS} = -6V, f = 1MHz$		540		μF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -6V, f = 1MHz$		390		μF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		22		ns
Rise Time	t_r	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		145		ns
Fall Time	t_f	See specified Test Circuit.		128		ns
Total Gate Charge	Q_g	$V_{DS} = -6V, V_{GS} = -4.5V, I_D = -7A$		18		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -6V, V_{GS} = -4.5V, I_D = -7A$		2.8		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS} = -6V, V_{GS} = -4.5V, I_D = -7A$		4.9		nC
Diode Forward Voltage	V_{SD}	$I_S = -7A, V_{GS} = 0V$		-0.78	-1.2	V

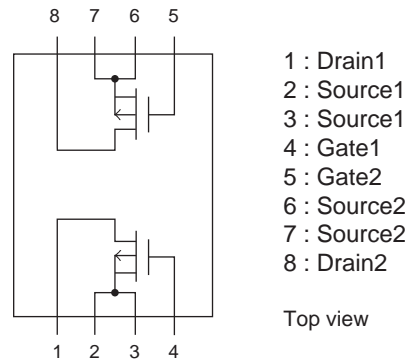
Package Dimensions

unit : mm (typ)

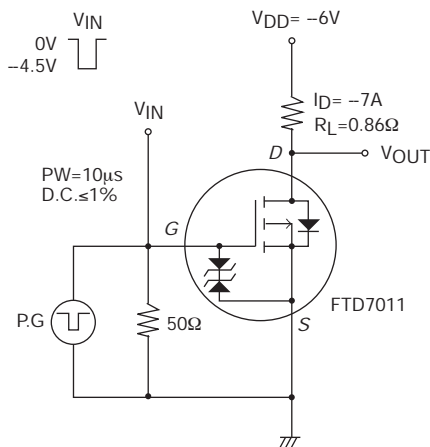
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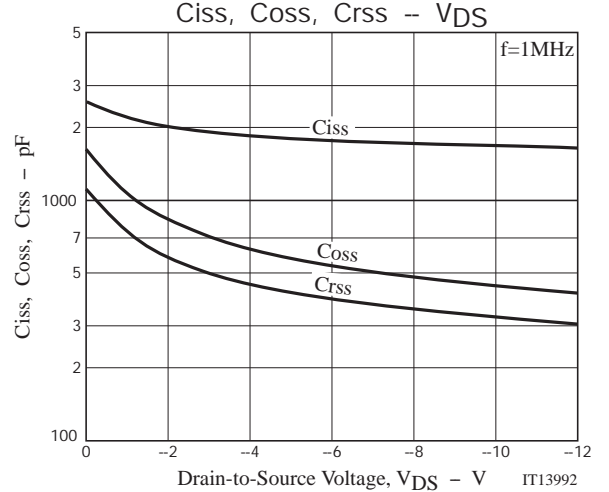
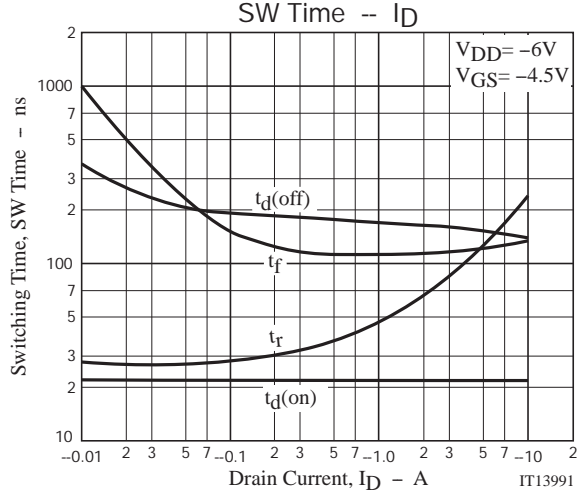
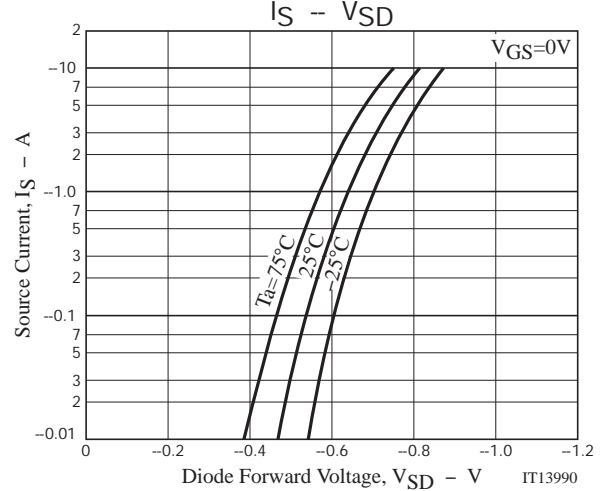
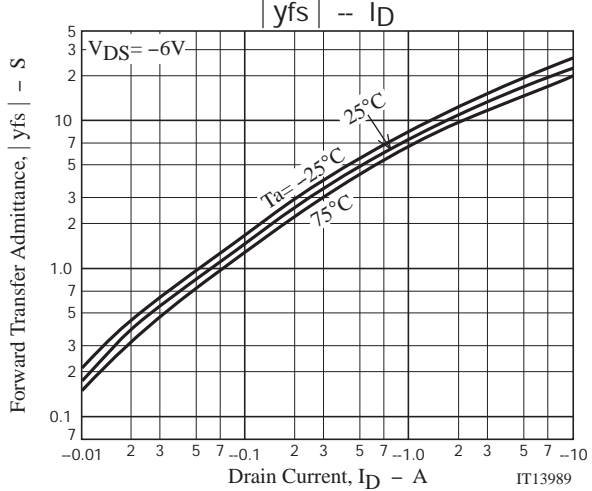
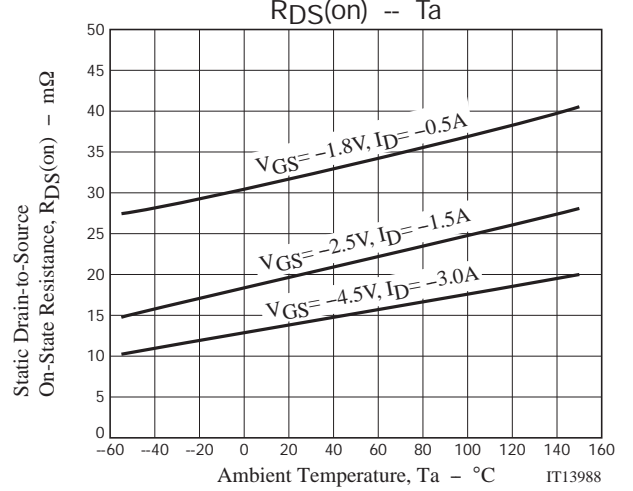
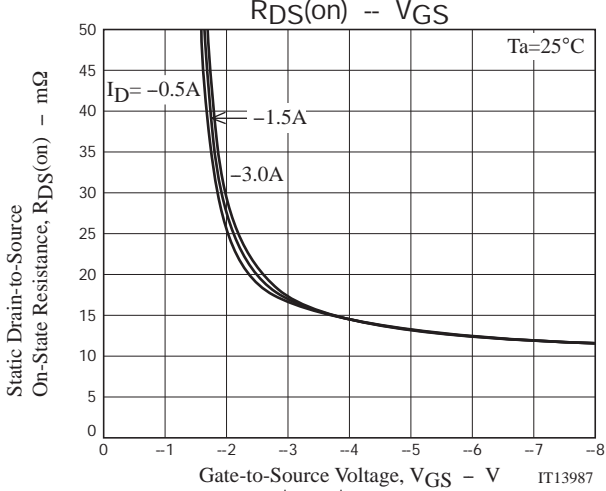
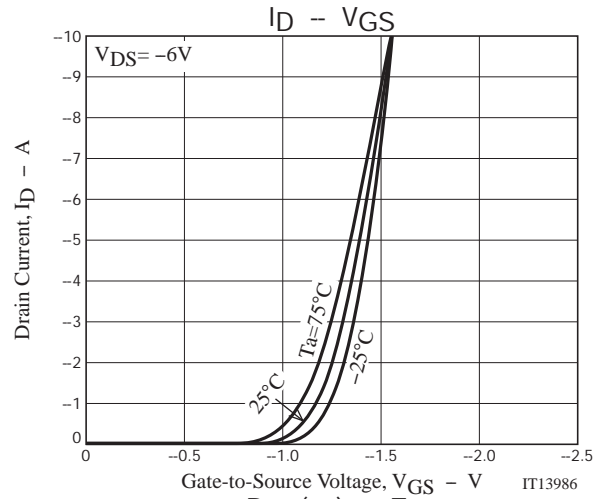
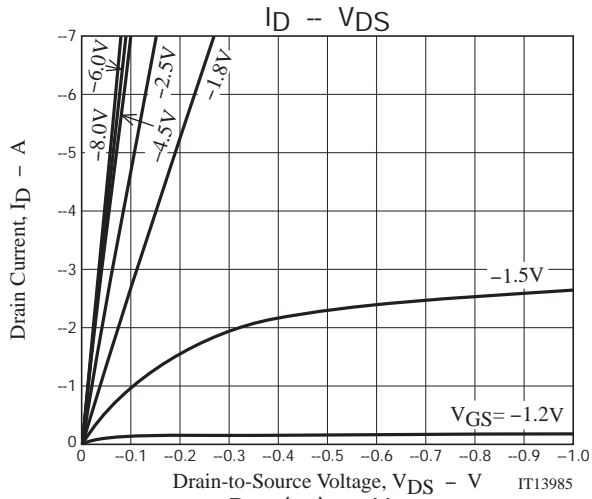


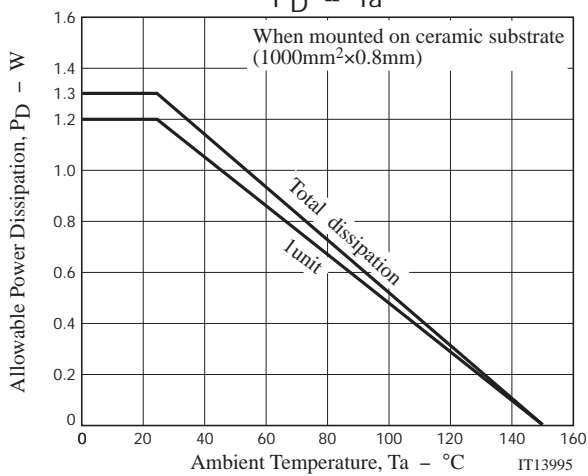
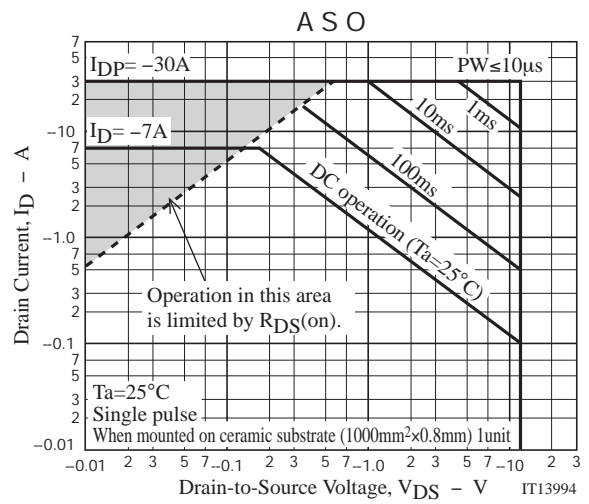
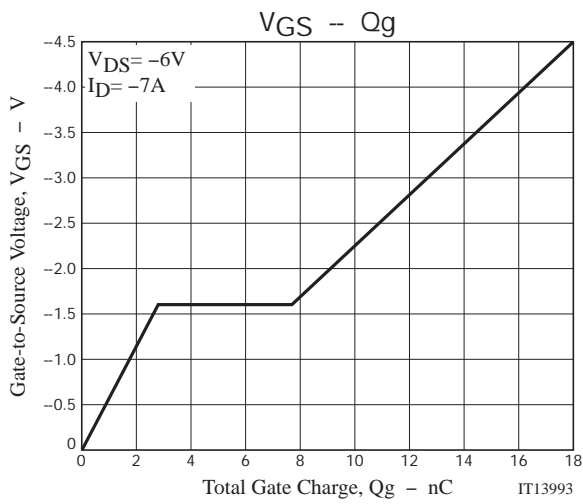
Electrical Connection



Switching Time Test Circuit







Note on usage : Since the FTD7011 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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